Systematic Comparison of the Raman Spectra of Metallic and Semiconducting SWNTs

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Raman spectra of individual SWNTs were systematically investigated by comparing the behavior of 21 semiconducting and 32 metallic SWNTs. It is found that, compared to semiconducting SWNTs, the RBM of metallic ones is softened, which exhibits chirality dependence. There are significant differences in the line shape of the G-band between semiconducting and metallic SWNTs, which was attributed to electron–phonon coupling previously. However, we found that the differences cannot be explained only by the electron–phonon coupling via the Kohn anomaly mechanism. Curvature effect and other unknown reasons appear to also contribute to the dissimilarities. As for the D-band, the frequency of metallic SWNTs does not show a softening effect when compared with that of semiconducting SWNTs, which is not consistent with theoretical predictions.

Single-walled carbon nanotube (SWNT) is a unique 1-D system obtained by wrapping a graphene sheet into a seamless cylinder. Different from graphene, SWNTs can be metallic or semiconducting, depending on the wrapping direction which is specified by chiral index \((n, m)\). These geometry-determined differences in electronic density of states (EDOS) around the Fermi level may give rise to subtle differences in some of their physical properties, such as the Raman spectra of SWNTs.

Raman spectroscopy is an important aspect in the research of SWNTs, and also a powerful tool in characterizing SWNTs. Generally, there are three important features in Raman spectra of SWNTs: the radial breathing mode (RBM), where all carbon atoms vibrate in phase in the radial direction; the tangential G-band, which consists of vibrations of carbon atoms along the tube axis (LO phonon mode) or along the circumferential direction (TO phonon mode) of SWNTs; and the D-band, which is originated from disorder. RBM is the unique Raman active mode of SWNTs compared to other graphitic carbon systems, and is supposed to be an indication of SWNTs. Both theoretical and experimental studies have shown that the frequency of RBM is inversely proportional to the diameter of SWNTs. G-Band is another widely studied Raman active mode of SWNTs, typically the TO and LO phonon modes giving rise to two separate peaks, where the higher energy peak and lower energy peak are called \(G^+\) and \(G^-\) respectively. D-Band, different from RBM and G-band, is due to a double resonant process. Its intensity is mainly used to characterize the defects in SWNTs and other carbon materials.

In recent years there have been many investigations on the G-band of metallic SWNTs. Experimental reports have shown that the frequency and line width of the \(G^-\) peak of metallic SWNTs are very sensitive to the position of their Fermi level due to the electron–phonon coupling via the Kohn anomaly mechanism. In contrast, investigation of the G-band in semiconducting SWNTs as a comparison has been rare. Comparisons for the RBM and D-band between individual metallic and semiconducting SWNTs and insights into the differences are also lacking. The comparisons between Raman spectra of SWNTs with and without electrons at the Fermi level may bring some interesting and unexpected observations and contribute to gain deeper insights into Raman spectra of SWNTs.

In this article, Raman spectra of individual SWNTs were systematically investigated by comparing the behavior of semiconducting and metallic SWNTs. Raman spectra of 53 individual SWNTs were analyzed. It is found that, compared to semiconducting SWNTs, the RBM of metallic ones is softened, which exhibits chirality dependence. There are significant differences in the line shape of the G-band between semiconducting and metallic SWNTs, which was attributed to electron–phonon coupling previously. However, we found that the differences cannot be explained only by the electron–phonon coupling via the Kohn anomaly mechanism. Curvature effect and other unknown reasons appear to also contribute to the dissimilarities. As for the D-band, the frequency of metallic SWNTs does not show a softening effect when compared with that of semiconducting SWNTs.

SWNTs were grown directly on Si (111) surfaces with a 200 nm thick SiO\(_2\) layer by chemical vapor deposition (CVD). Briefly, Fe(OH)\(_3\) colloids hydrolyzed from FeCl\(_3\) were spin-coated onto Si surfaces to act as the catalysts, and the growth was carried out at 775 °C for 5 min with a flow of ethene at 10 standard cubic centimeters per minute (sccm), and hydrogen and argon at 600 sccm, respectively. There is a significantly low density of SWNTs (shown in Figure S1, Supporting Information), so that Raman spectra from just one individual SWNT are observed. From AFM imaging, the diameters of the as-grown carbon nanotubes are mainly in the range of 1–2 nm. Raman spectral characterization was performed by using Renishaw 1000 micro-Raman spectroscopy (~1 μm spot size) with a 632.8 nm (1.959 eV) He-Ne laser with laser power of 8 mW. To ensure that SWNTs were examined parallel to laser polarization direction, lithographically etching markers were used for the measurements.
alignment. All the Raman spectra were fitted to Lorentzian line shape to obtain the peak frequency, intensity and full width at half-maximum (fwhm). Chiral indices \((n, m)\) were assigned based on the characteristic frequency, intensity and fwhm of RBM.\(^{15}\)

Figure 1 shows the RBM and G-band spectra of two individual SWNTs. The spectra with frequency of RBM \(\omega_{\text{RBM}}\) at 145 cm\(^{-1}\) indicate a semiconducting SWNT (1# SWNT) according to the Kataura plot.\(^{16}\) The G-band is characteristic of semiconducting SWNTs and can be well fitted by two Lorentzian peaks. The \(G^+\) and \(G^-\) of this semiconducting SWNT \((G^+_S\) and \(G^-_S)\) are located at 1593 and 1576 cm\(^{-1}\), with narrow line width of 10 and 8 cm\(^{-1}\) respectively. And the intensity of \(G^+_S\) is much stronger than that of \(G^-_S\), where the peak intensity ratio of \(G^+_S\) to \(G^-_S\) is about 6.8. The spectra with \(\omega_{\text{RBM}}\) at 198 cm\(^{-1}\) correspond to a metallic SWNT (2# SWNT). The G-band does not show BWF line shape as reported\(^{10,17,18}\) and can also be fitted by two Lorentzian peaks. Its \(G^+\) and \(G^-\) \((G^+_M\) and \(G^-_M)\) are located at 1581 and 1565 cm\(^{-1}\), with broad line width of 13 and 12 cm\(^{-1}\) respectively. In contrast to the semiconducting 1# SWNT, the intensity of \(G^-_M\) is just stronger than that of \(G^+_M\), where the peak intensity ratio of \(G^+_M\) to \(G^-_M\) is 1.592 (see Table S1 in Supporting Information). As will be discussed in the following, these differences are representative for the SWNTs we studied. Overall we have obtained Raman spectra from 53 individual SWNTs, 21 of which are semiconducting and 32 are metallic.

In Figure 2A, the frequency of RBM \(\omega_{\text{RBM}}\) of 53 individual SWNTs as a function of inverse diameter \((1/d)\) is plotted. The diameters are calculated from chiral indices \((n, m)\), which are assigned based on their RBM.\(^{15}\) The black squares are semiconducting SWNTs, and the red squares are metallic ones. The blue line is linearly fitted from \(\omega_{\text{RBM}}\) of all 53 SWNTs. Closer examination reveals that \(\omega_{\text{RBM}}\) of semiconducting SWNTs are mostly above the fitting line, whereas \(\omega_{\text{RBM}}\) of metallic SWNTs are below the fitting line. This can be seen more clearly in Figures 2B and 2C, where \(\omega_{\text{RBM}}\) of semiconducting and metallic SWNTs as a function of \(1/d\) are plotted and fitted separately with \(\omega_{\text{RBM}}(\text{cm}^{-1}) = A/d + B\). We obtained the relation \(\omega_{\text{RBM}}^S(\text{cm}^{-1}) = 223.4/d(\text{nm}) + 12.6\) for semiconducting SWNTs resonant with \(E_1^S\), and \(\omega_{\text{RBM}}^M(\text{cm}^{-1}) = 218.3/d(\text{nm}) + 15.9\) for metallic SWNTs resonant with \(E_1^M\). The value \(A\) for metallic SWNTs is smaller than that for semiconducting SWNTs. First principle calculations\(^{19}\) using density functional theory have predicted a similar trend: metallic SWNTs generally exhibited lower \(\omega_{\text{RBM}}\) with similar diameters. Another simulation based on ensemble Monte Carlo technique showed that RBM damped the charge transport property to some extent, indicating a coupling between RBM and electrons around the Fermi level.\(^{20}\)

It is known that, for semiconducting SWNTs, electrons can only be excited optically between one pair of van Hove singularities \((E_\text{II}^S, E_\text{III}^S, \ldots)\); however for metallic SWNTs, besides electrons at van Hove singularities \((E_\text{II}^M, E_\text{III}^M, \ldots)\), electrons around the Fermi level can be excited to available states \((E_{\text{II}}^M)\). These electrons, when interacting with phonons of specific energies, can lead to the modified frequencies and lifetimes for the phonons. A. Jorio\(^{21}\) proposed the following functional form, 

\[
\omega_{\text{RBM}} (\text{cm}^{-1}) = A/d (\text{nm}) + B + (C + D \cos^2 3\theta)/d^2,
\]

where \(A\) described the elastic behavior of SWNTs. Hence from our result it is suggested that electron–phonon coupling lowers the elastic constants, making metallic SWNTs have smaller constant \(A\) than semiconducting ones. One more interesting phenomenon stands out in Figure 2D, where deviation of experimental \(\omega_{\text{RBM}}\) of metallic SWNTs from \(\omega_{\text{RBM}}(\Delta \omega_{\text{RBM}} = \omega_{\text{RBM}} - \omega_{\text{RBM}}^M)\) is plotted as a function of chiral angle \(\theta\), and from this figure we can see that metallic SWNTs close to armchair are more softened than those close to zigzag ones, indicating that the softening of RBM has some correlations with the chirality of the SWNT.

Figure 3 shows the frequency, line width and intensity of the G-band spectra of 53 individual SWNTs. Theoretical studies\(^{12,22–24}\) have shown that for semiconducting SWNTs \(G^+_S\) and \(G^-_S\) correspond to LO and TO phonon modes respectively; in contrast, the \(G^+_M\) and \(G^-_M\) for metallic SWNTs should be respectively assigned to TO and LO phonon modes, since the electron–phonon coupling effect softens the LO phonon mode but not of the circumferential TO mode. Therefore we compare \(G^+_S\) with \(G^-_S\) since they are LO phonon modes and \(G^-_M\) with \(G^+_M\) since they are TO phonon modes. The observation in Figure 3A has very interesting implications. First, as there is no diameter dependence for the \(G^+_M\) (a similar result was observed by A. Jorio\(^{21}\)), it suggests that the TO phonon mode of metallic SWNTs is not affected by the curvature effects, as do the semiconducting SWNTs of similar diameter. This is surprising, and the reason for this needs further investigation. Second, if the downshift of the \(G^-_S\) relative to \(G^+_S\) is due to curvature effect alone, the asymptote value of 1583.7 cm\(^{-1}\) should be the average frequency of the \(G^+_S\). However, from Figure 3B one can see that the average frequency of \(G^+_S\) is 1593 cm\(^{-1}\) (independent of diameter), which is consistent with previous experimental results,\(^{3}\) but this value is higher than the results obtained by theoretical calculations.\(^{25,26}\) This suggests there exist additional effect(s) for the upshift of the \(G^+_S\) that are not considered in the theoretical calculations. In addition to the frequency of \(G^+_S\) as a function of inverse diameter, Figure 3B also shows the frequency of \(G^-_M\), since both correspond to the LO phonon mode. The frequency of \(G^+_S\) is at around 1593 cm\(^{-1}\), independent of diameter and chiral angle. But the frequency of \(G^-_M\) is much lower (≈35 cm\(^{-1}\) lower on average) than that of \(G^+_S\).
The Kohn anomaly is suppressed. This is consistent with our level being away from the band crossing point, which means that \( \Delta \omega \) is resonant with \( \omega_0 \) based on (A) all 53 SWNTs resonant with \( E_1 \) as a function of inverse diameter \( (1/d) \). (D) Deviation of experimental \( \omega_{RBM} \) of metallic SWNTs from blue lines in (C) as a function of chiral angle \( (\theta) \). Black and red squares are semiconducting and metallic SWNTs respectively. Blue lines are fitting curves respectively based on (A) all 53 SWNTs, (B) 18 semiconducting SWNTs, and (C) 32 metallic SWNTs. (B and C): Chiral indices are determined from RBM.

Figure 2. Frequency of RBM (\( \omega_{RBM} \)) for (A) all 53 SWNTs, (B) 18 semiconducting SWNTs resonant with \( E_1 \) as a function of inverse diameter \( (1/d) \). (D) Deviation of experimental \( \omega_{RBM} \) of metallic SWNTs from blue lines in (C) as a function of chiral angle \( (\theta) \). Black and red squares are semiconducting and metallic SWNTs respectively. Blue lines are fitting curves respectively based on (A) all 53 SWNTs, (B) 18 semiconducting SWNTs, and (C) 32 metallic SWNTs. (B and C): Chiral indices are determined from RBM.

Figure 3. Lorentzian fitting results of the G-band for all 53 SWNTs as a function of inverse diameter \( (1/d) \): (A) frequency of the TO phonon mode-based \( G_1^- \) and \( G_1^+ \); (B) frequency of the LO phonon mode-based \( G_2^- \) and \( G_2^+ \); (C) \( \omega_0^+ - \omega_0^- \); (D) line width of the LO phonon mode-based \( G_2^- \) and \( G_2^+ \); (E) line width of the TO phonon mode-based \( G_1^- \) and \( G_1^+ \); (F) peak intensity ratio of LO to TO phonon mode. Inset of F: peak intensity ratio of LO to TO phonon mode of metallic SWNTs as a function of chiral angle. Black and red squares are semiconducting and metallic SWNTs respectively. Blue lines are fitting curves respectively based on frequencies of \( G_5^- \), \( G_5^+ \), and \( \omega_0^+ - \omega_0^- \) of semiconducting SWNTs.

and is dependent on diameter. This is consistent with the softening due to electron–phonon coupling via the Kohn anomaly mechanism.\(^{27}\) We use the relation \( \omega G = C - D/d \) to fit the frequency value of \( \omega_0 \), and get \( C = 1582.9 \) cm\(^{-1}\) and \( D = 21.0 \). With this value \( D \) it suggests that the Fermi level is away from the band crossing point, which means that the Kohn anomaly is suppressed. This is consistent with our line width observation (see discussion in the following). Figure 3C shows the \( \Delta \omega_G \) as a function of \( 1/d \). The \( \Delta \omega_G \) of semiconducting SWNTs follows a relation of \( 1/d^2 \) (the blue fitting curve). It is observed that \( \Delta \omega_G \) of metallic SWNTs are below the fitting curve, which means that \( \Delta \omega_G \) of metallic SWNTs are smaller than that for semiconducting ones. This observation is different from previous observations\(^{7} \) where a larger frequency separation \( \Delta \omega_G \) between the \( G^+ \) and \( G^- \) in metallic SWNTs was reported. Since the curvature effect is not present in the metallic SWNTs as discussed previously, the only other known factor contributing to the frequency separation \( \Delta \omega_G \) is the electron–phonon coupling due to the Kohn anomaly mechanism. The relatively small \( \Delta \omega_G \) is consistent with the fact that these metallic SWNTs are doped, and the Fermi level is away from the band crossing point.

It is reported\(^{22,27} \) that the electron–phonon coupling effect can give rise to broadened line width of \( G_5^- \) since the LO phonon mode can decay into low-energy electron–hole excitations around the band crossing point and thus the lifetime of the phonon is reduced. As shown in Figure 3D, the average line width of \( G_5^- \) and \( G_5^+ \) (both are LO phonon mode) is 16 and 11 cm\(^{-1}\) respectively, with an average broadening of \( \sim 5 \) cm\(^{-1}\), which has not been found when the LO phonon mode is Lorentzian shape.\(^{28} \) In fact, theoretical calculations have predicted a line width of \( 60 \) cm\(^{-1}\) at zero doping for a (9,9) SWNT.\(^{27} \) Since the metallic SWNTs in our experiments are of similar diameter, the maximum broadening should be about the same. The 5 cm\(^{-1}\) broadening in our experiments is consistent with the conclusion that the metallic SWNTs are doped and their Fermi levels are away from their band crossing point. Besides, it is noticed that the average line width of \( G_5^+ \) is broadened by 8 cm\(^{-1}\), compared to that of \( G_5^- \) (both are TO phonon mode), which is shown in Figure 3E. Putting this observation together with the downshift of \( G_5^+ \) relative to \( G_5^- \), it is convincing that there are some other reasons for the differences in the line width between \( G_5^+ \) and \( G_5^- \), which needs further exploration.
A remarkable decrease in the intensity of \( G \) bands has only 24 SWNTs have observed as suspended SWNTs recently reported.\(^3\) It may be that the intensity of the LO phonon mode will bring about the remarkable decay of semiconducting SWNTs are larger than 4.0, which means that the intensity of \( G \) bands is much higher than that of \( G \) bands, whereas the IRM for metallic SWNTs are mostly around 1.0, meaning \( G \) has almost the same intensity as \( G \). It is noted that there is no obvious difference in the intensity of \( G \) and \( G \), but a remarkable decrease in the intensity of \( G \) compared to that of \( G \) (Table S1 shown in Supporting Information). The similar intensity of \( G \) and \( G \) indicates that the difference between the intensity of \( G \) and \( G \) is not due to resonant conditions. Rather it may be interpreted by shorter lifetime of the LO phonon mode due to electron–phonon coupling. It is known that the intensity of resonant Raman spectra can be calculated using the equation:\(^2\)

\[
I(E_i) = \int \frac{Mg(E)}{(E_{\text{simple}} - E_i - i\gamma)(E_{\text{simple}} + E_{\text{ph}} - E_i - i\gamma)} \, dE
\]

where \( \gamma \) is the inverse lifetime of the phonon. Hence, the shorter lifetime of the LO phonon mode will bring about the remarkable decrease in the intensity of \( G \). However, as shown in the inset of Figure 3F, the chiral angle dependence of IRM is not observed as suspended SWNTs recently reported.\(^3\) It may be due to the interaction between SWNTs and substrate here.

Figure 4A shows frequencies of the D-band (\( \omega_D \)) as a function of 1/d. Since SWNTs directly grown by thermal CVD exhibit fewer defects, only 24 SWNTs have D-band and are presented here. The linear fitting shows that \( \omega_D \) of semiconducting SWNTs are inversely proportional to the diameter,\(^3\) with an equation \( \omega_D = 1345.6 - 33.6/d \) (nm). However, for metallic SWNTs, the frequency values are above the fitting curve, which means that the D-band of metallic SWNTs is hardened relative to that of semiconducting SWNTs; while in ref 32 the same equation was followed by semiconducting and metallic SWNTs.\(^3\) Although theoretical calculations under the Kohn anomaly mechanism have predicted a stronger softening for the \( A_1 \) mode at K point in graphite\(^3\) (which corresponds to the D-band phonon mode), we believe that the reason why D-band softening in metallic SWNTs cannot be observed is that the D-band Raman spectrum is double resonance in nature. As a result, the corresponding phonon that gives rise to D-band spectra is not exactly at the K point, but with a wavevector \( K + k \), where \( k \) is proportional to the laser excitation energy. From the theoretical prediction,\(^2\) the phonon softening is greatly reduced as the phonon wavevector moves away from the K point. Therefore it is reasonable that the phonon softening is not observed in metallic nanotubes. However, the hardening is unexpected too. At present we do not have a good explanation for this result. In Figures 4B and 4C, the intensity and the line width of the D-band as a function of 1/d are plotted. Since the intensity is related to both resonant conditions and defect numbers, there is not a clear difference between the semiconducting SWNTs and metallic SWNTs. But the line width of most semiconducting SWNTs is broader than that of metallic SWNTs. This is opposite to the G-band. It seems that the softening/hardening of the Raman active mode will be accompanied by the broadening/narrowing of the line width.

Although most metallic SWNTs have Raman spectra different from semiconducting ones, we have also observed another four abnormal metallic SWNTs. As shown in Figure 5, one metallic SWNT (3# SWNT), with \( \omega_D \) at 199 cm\(^{-1}\), is thought to have the same chirality as 2# SWNT shown in Figure 1A. The G-band can be well fitted by two Lorentzian peaks. Its \( G \) and \( G \) are located at 1596 and 1571 cm\(^{-1}\), with line width of 13 and 19 cm\(^{-1}\) respectively. And the intensity of \( G \) is much stronger than that of \( G \), where the peak intensity ratio of \( G \) to \( G \) is 20.4 (see Table S1 in Supporting Information). The G-band for 3# SWNT differs significantly from that for 2# SWNT, but is characteristic of G-band for 1# SWNT. This has been observed in ultralong SWNTs\(^3\) and other individual SWNTs,\(^3\) where the author\(^3\) suggested that individual SWNTs had the same line shape, irrespective of semiconducting or metallic ones. Our experiment results contradict that argument. In most cases, G-bands for semiconducting and metallic SWNTs have different line shape. As for the four abnormal SWNTs, we believe that it is due to the unintentional doping during the fabrication processing or \( O_2 \) adsorption that leads to electron transfer from metallic SWNTs and weakens the electron–phonon coupling.\(^1\) This makes it complicated to know whether a SWNT is
semiconducting or metallic from G-band. It is safe to determine a SWNT is metallic from G-band if electron–phonon coupling has a dramatic effect; however it is dangerous to determine a SWNT is semiconducting from G-band if electron–phonon coupling effect is not observed.

In summary, Raman spectra of individual semiconducting and metallic SWNTs were systematically compared in this article. Raman spectra of 53 individual SWNTs were analyzed. It is found that the RBM modes of the metallic SWNTs are softened compared to semiconducting SWNTs of similar diameter, which exhibits a chirality dependence. There are significant differences in the line shape of the G-band between semiconducting and metallic SWNTs. For the frequency, TO phonon-based $G^-$ is $1/E^2$ dependent due to curvature effect, while LO phonon-based $G^-\text{M}$ does not have diameter dependence, the reason for which is unknown at present. LO phonon-based $G^-\text{M}$ is inversely proportional to diameter due to electron–phonon coupling, while LO phonon-based $G^+\text{M}$ does not have diameter dependence, which is consistent with previous reports; however the frequency of $G^+\text{M}$ seems higher than theoretical calculations. The line widths of G-band of metallic SWNTs are broadened, where $G^-\text{M}$ can be attributed to electron–phonon coupling, but the reason for $G^-\text{M}$ broadening is not clear. The D-band frequency of metallic SWNTs does not show a softening effect when compared with that of semiconducting SWNTs, which is not consistent with theoretical predictions. Finally, we observed abnormal G-band of another four metallic SWNTs, which was not affected by electron–phonon coupling, and it might be O$_2$ adsorption or other unintentional doping that eliminated its effect. Therefore it is necessary to consider their exposure to adsorption or other unintentional doping that eliminated its effect.

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Supporting Information Available: Figure showing the sample and tables showing the fitting data. This material is available free of charge via the Internet at http://pubs.acs.org.

References and Notes

(8) In fact, the TO and LO phonon modes each have 3 different symmetries, A1, E1, and E2, so the G" and G^ can each contain up to three peaks. Usually only the A symmetry peaks show up.
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